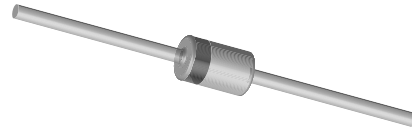


Zener Diodes

Features

- Silicon Planar Power Zener Diodes
- For use in stabilizing and clipping circuits with high power rating
- Standard Zener voltage tolerance is $\pm 5\%$
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



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Applications

- Voltage stabilization

Mechanical Data

Case: DO-41 Glass case

Weight: approx. 310 mg

Packaging Codes/Options:

TR / 5 k per 13" reel, 25 k/box

TAP / 5 k per Ammo pack (52 mm tape), 25 k/box

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Power dissipation		P_{tot}	1.3 ¹⁾	W
Z-current		I_Z	P_V/V_Z	mA

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R_{thJA}	110 ¹⁾	K/W
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 200\text{ mA}$	V_F			1.2	V

1N4728A to 1N4764A



Vishay Semiconductors

Electrical Characteristics

1N4728A...1N4764A

Partnumber	Nominal Zener Voltage ¹⁾	Test Current	Maximum Dynamic Impedance			Maximum Reverse Leakage Current		Surge Current ³⁾	Maximum Regulator Current ²⁾
	V_Z at I_{ZT}		Z_{ZT} at I_{ZT}	Z_{ZK} at I_{ZK}	I_{ZK}	I_R	Test Voltage V_R		
	V	mA	Ω	Ω	mA	μA	V	at $T_A = 25^\circ C$ I_R	mA
1N4728A	3.3	76	10	400	1	100	1	1380	276
1N4729A	3.6	69	10	400	1	100	1	1260	252
1N4730A	3.9	64	9	400	1	50	1	1190	234
1N4731A	4.3	58	9	400	1	10	1	1070	217
1N4732A	4.7	53	8	500	1	10	1	970	193
1N4733A	5.1	49	7	550	1	10	1	890	178
1N4734A	5.6	45	5	600	1	10	2	810	162
1N4735A	6.2	41	2	700	1	10	3	730	146
1N4736A	6.8	37	3.5	700	1	10	4	660	133
1N4737A	7.5	34	4	700	0.5	10	5	605	121
1N4738A	8.2	31	4.5	700	0.5	10	6	550	110
1N4739A	9.1	28	5	700	0.5	10	7	500	100
1N4740A	10	25	7	700	0.25	10	7.6	454	91
1N4741A	11	23	8	700	0.25	5	8.4	414	83
1N4742A	12	21	9	700	0.25	5	9.1	380	76
1N4743A	13	19	10	700	0.25	5	9.9	344	69
1N4744A	15	17	14	700	0.25	5	11.4	304	61
1N4745A	16	15.5	16	700	0.25	5	12.2	285	57
1N4746A	18	14	20	750	0.25	5	13.7	250	50
1N4747A	20	12.5	22	750	0.25	5	15.2	225	45
1N4748A	22	11.5	23	750	0.25	5	16.7	205	41
1N4749A	24	10.5	25	750	0.25	5	18.2	190	38
1N4750A	27	9.5	35	750	0.25	5	20.6	170	34
1N4751A	30	8.5	40	1000	0.25	5	22.8	150	30
1N4752A	33	7.5	45	1000	0.25	5	25.1	135	27
1N4753A	36	7	50	1000	0.25	5	27.4	125	25
1N4754A	39	6.5	60	1000	0.25	5	29.7	115	23
1N4755A	43	6	70	1500	0.25	5	32.7	110	22
1N4756A	47	5.5	80	1500	0.25	5	35.8	95	19
1N4757A	51	5	95	1500	0.25	5	38.8	90	18
1N4758A	56	4.5	110	2000	0.25	5	42.6	80	16
1N4759A	62	4	125	2000	0.25	5	47.1	70	14
1N4760A	68	3.7	150	2000	0.25	5	51.7	65	13
1N4761A	75	3.3	175	2000	0.25	5	56	60	12
1N4762A	82	3.0	200	3000	0.25	5	62.2	55	11
1N4763A	91	2.8	250	3000	0.25	5	69.2	50	10
1N4764A	100	2.5	350	3000	0.25	5	76.0	45	9

¹⁾ Based on dc-measurement at thermal equilibrium while maintaining the lead temperature (T_L) at $30^\circ C + 1^\circ C$, 9.5 mm (3/8") from the diode body.

²⁾ Valid provided that electrodes at a distance of 4 mm from case are kept at ambient temperature.

³⁾ $T_P = 10$ ms.

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

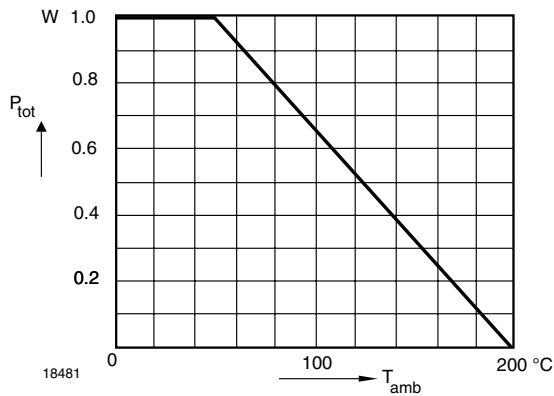


Figure 1. Admissible Power Dissipation vs. Ambient Temperature

Package Dimensions in mm (Inches)

